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CHANGCHUN NEW INDUSTRIES
OPTOELECTRONICS TECH.CO.,LTD.

658nm Laser Diode

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■ Features

- Output Power: 200mW (CW)
- Efficient Quantum Well Structure
- Standard TO-18 Package



■ Absolute Maximum Ratings

(Tc=25°C)

Item	Symbol	Absolute Maximum Ratings	Unit
Optical Output Power	Po	200	mW
LD Reverse Voltage	Vr (LD)	2	V
Storage Temperature	Tstg	-40~100	°C
Operating Case Temperature	Tc	-10~75	°C

■ Initial Electrical/Optical Characteristics

(Tc=25°C)

Item	Symbol	Typ.	Unit
Optical Output	Po	200	mW
Peak Wavelength*	λp	658±8	nm
Threshold Current	Ith	≤0.08	A
Operating Current	Iop	≤0.28	A
Slope Efficiency	η	≥0.95	W/A
Operating Voltage	Vop	≤2.8	V
Horizontal Beam Divergence	θ//	≤10	deg.
Vertical Beam Divergence	θ⊥	≤17	deg.
Spectrum FWHM		<0.2	
Wavelength Temperature Coefficient		0.2	nm/°C
Polarization		TE	

* Measuring specifications.

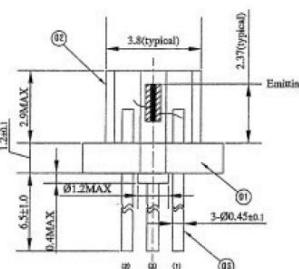
All figures in this specification are measured by CNI's method and may contain measurement deviations.

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The above specifications are for reference purpose only and subjected to change without prior notice.

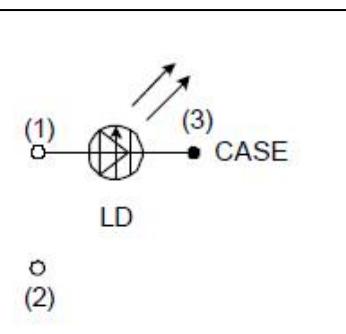
Outline Dimension

TO-18 Package



(Unit: mm)

Pin Connection



◆ CONTACT

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